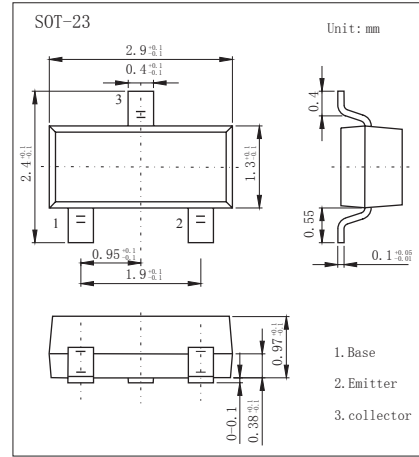


## PNP Transistors

### MMBTA92

■ Features

- High voltage transistor
- Low collector-emitter saturation voltage
- Complementary to MMBTA42 (NPN)



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V <sub>CB0</sub>	-300	V
Collector - Emitter Voltage	V <sub>CEO</sub>	-300	
Emitter - Base Voltage	V <sub>EBO</sub>	-5	
Collector Current - Continuous	I <sub>C</sub>	-500	mA
Collector Power Dissipation	P <sub>C</sub>	350	mW
Thermal Resistance Junction to Ambient	R <sub>θJA</sub>	417	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature range	T <sub>stg</sub>	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V <sub>CB0</sub>	I <sub>C</sub> = -100 μA, I <sub>E</sub> =0	-300			V
Collector- emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> = -1 mA, I <sub>B</sub> =0	-300			
Emitter - base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = -100 μA, I <sub>C</sub> =0	-5			
Collector-base cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = -200 V, I <sub>E</sub> =0			-0.25	uA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> =0			-0.1	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-20 mA, I <sub>B</sub> =- 2mA			-0.2	V
Base - emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -20mA, I <sub>B</sub> = -2mA			-0.9	
DC current gain	h <sub>fe</sub> (1)	V <sub>CE</sub> = -10V, I <sub>C</sub> = -1mA	60			
	h <sub>fe</sub> (2)	V <sub>CE</sub> = -10V, I <sub>C</sub> = -10mA	100		300	
	h <sub>fe</sub> (3)	V <sub>CE</sub> = -10V, I <sub>C</sub> =-30mA	60			
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -20V, I <sub>C</sub> = -10mA, f=30MHz	50			MHz

■ Classification of h<sub>fe</sub>(2)

Type	MMBTA92	MMBTA92-L
Range	100-300	100-200
Marking	2D	



炬芯微  
XUANXINWEI

SMD Type Transistors

PNP Transistors

MMBTA92

Typical Characteristics

